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(21) International Application Number: PCT/US96/15432 ✓ (22) International Filing Date: 25 September 1996 (25.09.96) ✓ (30) Priority Data: 08/535,701 28 September 1995 (28.09.95) ✓ US (71) Applicant: HOECHST CELANESE CORPORATION [US/US]; Route 202-206 North, Sommerville, NJ 08876 (US). (72) Inventors: RAHMAN, M., Dalil; 62 Concord Ridge Road, Flemington, NJ 08822 (US). AUBIN, Daniel, P.; 202 Congdon Road, Voluntown, CT 06384 (US). (74) Agents: SAYKO, Andrew, F., Jr. et al.; Hoechst Celanese Corporation, 70 Meister Avenue, Sommerville, NJ 08876 (US).	(81) Designated States: CN, JP, KR, (SG) European patent (AT, BE, CH, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE). Published <i>With international search report. Before the expiration of the time limit for amending the claims and to be republished in the event of the receipt of amendments.</i>	
(54) Title: LOW METAL ION CONTAINING 4,4'-(1-(4-(1-(4-HYDROXYPHENYL)-1-METHYLETHYL)PHENYL)ETHYLIDENE)BISPHENOL AND PHOTORESIST COMPOSITIONS THEREFROM		
(57) Abstract The present invention provides methods for producing TPPA having low level of metal ions, utilizing treated ion exchange resins. A method is also provided for producing photoresist composition having a very low level of metal ions from such TPPA for producing semiconductor devices using such photoresist compositions.		